

# BCR25KM-12LB

# Triac

Medium Power Use

REJ03G1676-0100 Rev.1.00 Jun 05, 2008

### **Features**

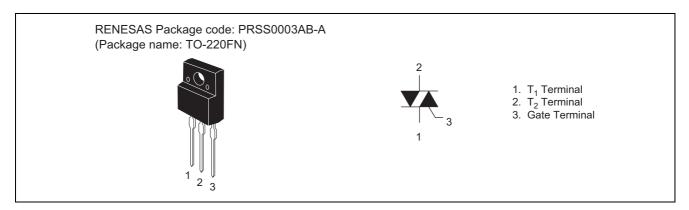
I<sub>T (RMS)</sub>: 25 A
 V<sub>DRM</sub>: 600 V

 $\bullet \quad I_{FGTI},\,I_{RGTI},\,I_{RGTIII}{:}\;50\;mA$ 

• V<sub>iso</sub>: 2000 V

- Insulated Type
- Planar Type

### **Outline**



## **Applications**

Contactless AC switch, electric heater control, light dimmer, on/off and speed control of small induction motor, on/off control of copier lamp

# **Maximum Ratings**

| Parameter                                   | Symbol    | Voltage class | Unit  |  |
|---|-----------|---------------|-------|--|
| Faranietei                                  | Symbol    | 12            | Offic |  |
| Repetitive peak off-state voltage Note1     | $V_{DRM}$ | 600           | V     |  |
| Non-repetitive peak off-state voltage Note1 | $V_{DSM}$ | 720           | V     |  |

Notes: 1. Gate open.

| Parameter                      | Symbol               | Ratings     | Unit             | Conditions   |
|--------------------------------|----------------------|-------------|------------------|--|
| RMS on-state current           | I <sub>T (RMS)</sub> | 25          | Α                | Commercial frequency, sine full wave 360°            |
|                                |                      |             |                  | conduction, Tc = 62°C                                |
| Surge on-state current         | I <sub>TSM</sub>     | 250         | Α                | 50 Hz sinewave 1 full cycle, peak value,             |
|                                |                      |             |                  | non-repetitive                                       |
| I <sup>2</sup> t for fusion    | l <sup>2</sup> t     | 313         | A <sup>2</sup> s | Value corresponding to 1 cycle of half wave          |
|                                |                      |             |                  | 50Hz, surge on-state current                         |
| Peak gate power dissipation    | P <sub>GM</sub>      | 5           | W                |  |
| Average gate power dissipation | P <sub>G (AV)</sub>  | 0.5         | W                |  |
| Peak gate voltage              | $V_{GM}$             | 10          | V                |  |
| Peak gate current              | I <sub>GM</sub>      | 2           | Α                |  |
| Junction Temperature           | Tj                   | -40 to +150 | °C               |  |
| Storage temperature            | Tstg                 | -40 to +150 | °C               |  |
| Mass                           | _                    | 2.0         | g                | Typical value  |
| Isolation voltage              | V <sub>iso</sub>     | 2000        | V                | Ta = 25°C, AC 1 minute,                              |
|                                |                      |             |                  | T <sub>1</sub> • T <sub>2</sub> • G terminal to case |

## **Electrical Characteristics**

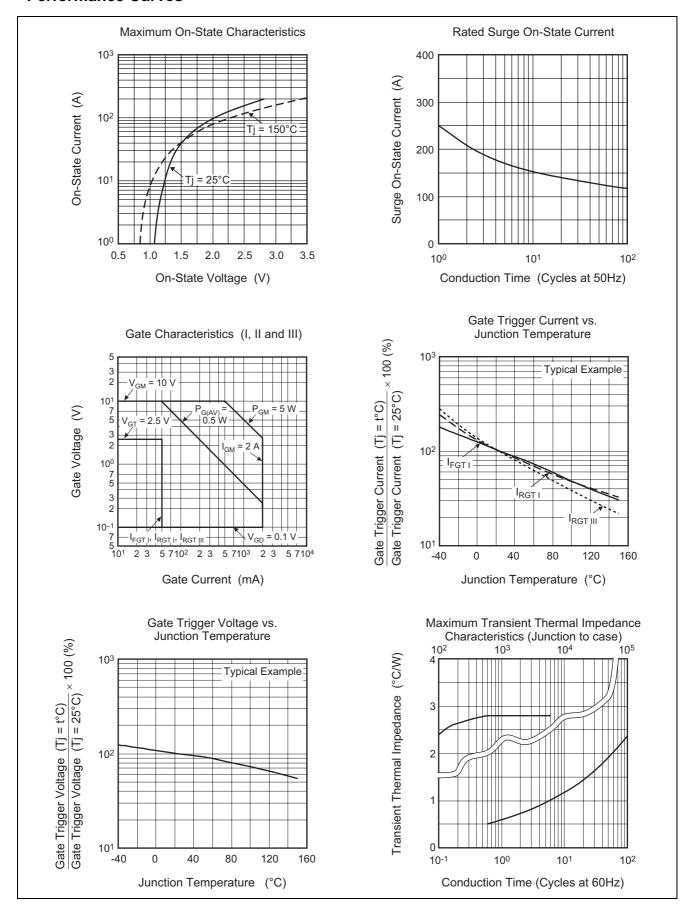
| Parameter   |         | Symbol                | Min.    | Тур. | Max.    | Unit | Test conditions                               |
|---|---------|-----------------------|---------|------|---------|------|---|
| Repetitive peak off-state of  | current | I <sub>DRM</sub>      | _       | _    | 3.0/5.0 | mA   | Tj = 125/150°C, V <sub>DRM</sub> applied      |
| On-state voltage  |         | $V_{TM}$              | _       | _    | 1.5     | V    | Tc = 25°C, I <sub>TM</sub> = 40 A,            |
|   |         |                       |         |      |         |      | instantaneous measurement                     |
| Gate trigger voltage <sup>Note2</sup>                                   | I       | $V_{FGTI}$            | _       |      | 2.0     | V    | $Tj = 25$ °C, $V_D = 6$ V, $R_L = 6$ Ω,       |
|   | II      | $V_{RGTI}$            | _       | _    | 2.0     | V    | $R_G = 330 \Omega$                            |
|   | III     | $V_{RGTIII}$          | _       | _    | 2.0     | V    |   |
| Gate trigger curent <sup>Note2</sup>                                    | I       | $I_{FGTI}$            | _       | _    | 50      | mA   | $Tj = 25$ °C, $V_D = 6$ V, $R_L = 6$ Ω,       |
|   | II      | $I_{RGT_{I}}$         | _       | _    | 50      | mA   | $R_G = 330 \Omega$                            |
|   | III     | I <sub>RGTIII</sub>   | _       | _    | 50      | mA   |   |
| Gate non-trigger voltage  |         | $V_{\sf GD}$          | 0.2/0.1 | _    | _       | V    | $Tj = 125/150^{\circ}C$ , $V_D = 1/2 V_{DRM}$ |
| Thermal resistance  |         | R <sub>th (j-c)</sub> | _       | _    | 2.8     | °C/W | Junction to case <sup>Note3</sup>             |
| Critical-rate of rise of off-state commutation voltage <sup>Note4</sup> |         | (dv/dt)c              | 10/1    |      | _       | V/μs | Tj = 125/150°C                                |

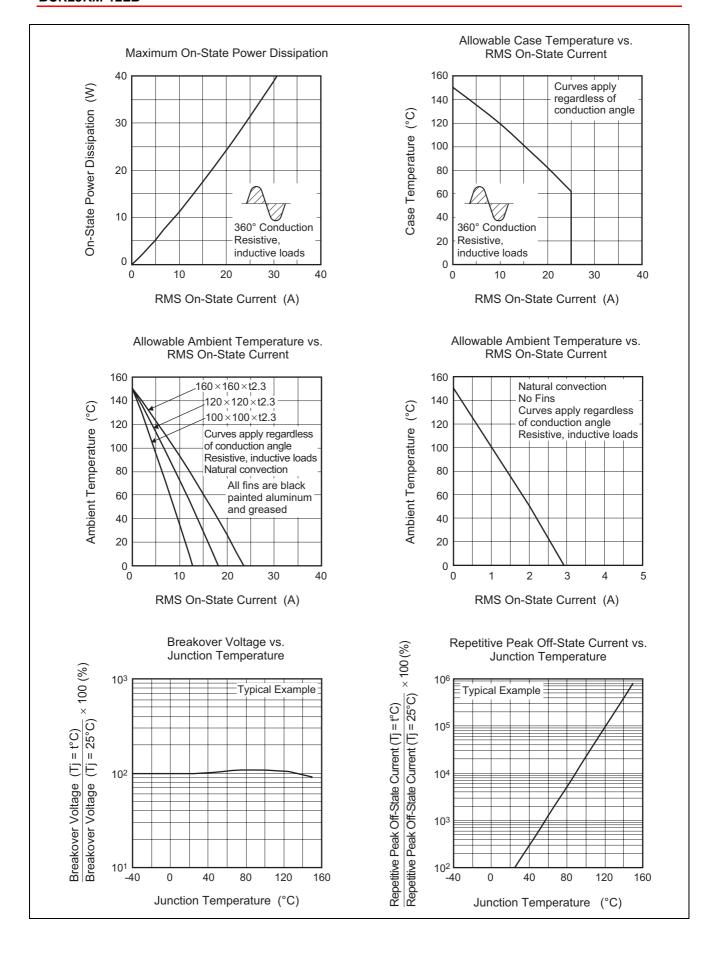
Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

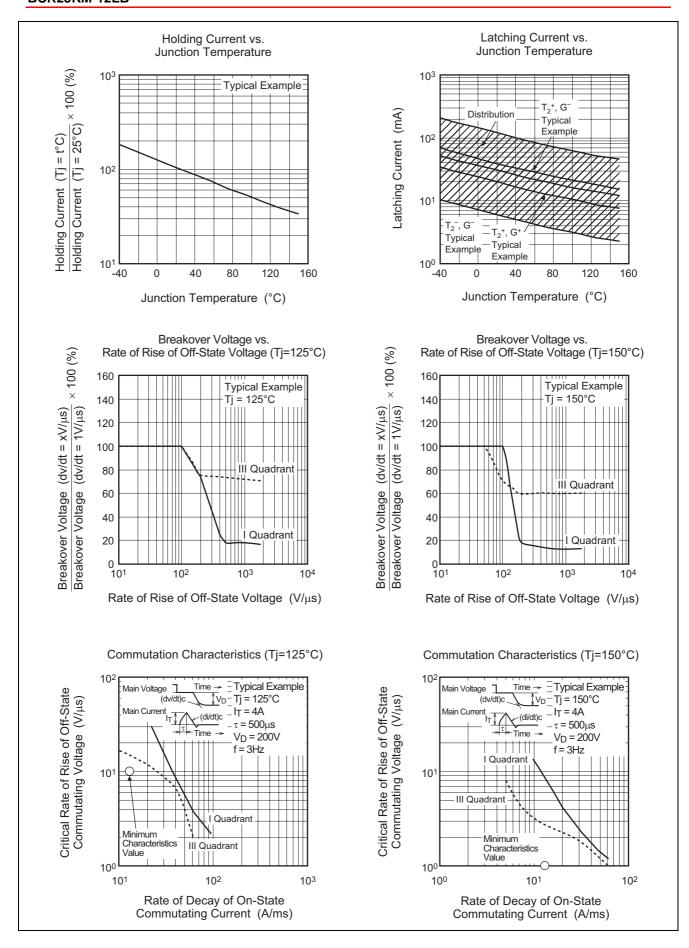
- 3. The contact thermal resistance  $R_{th\;(c\text{-}f)}$  in case of greasing is 0.5°C/W.
- 4. Test conditions of the critical-rate of rise of off-state commutation voltage is shown in the table below.

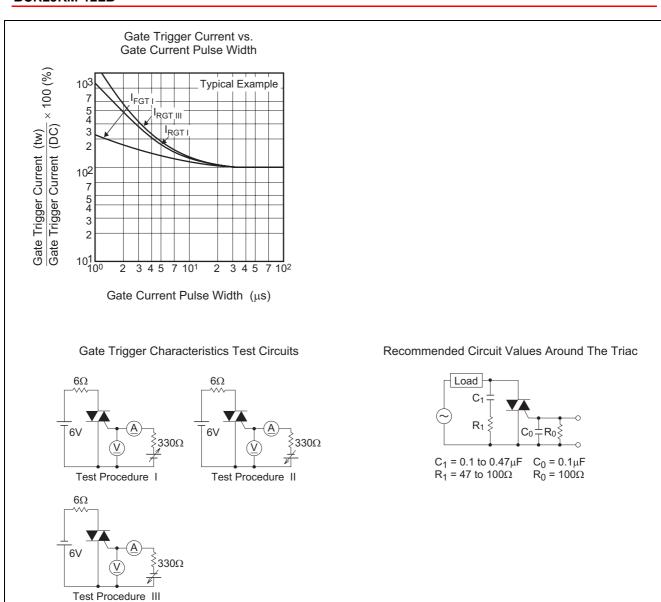
| Test conditions  | Commutating voltage and current waveforms (inductive load) |
|--|--|
| 1. Junction temperature Tj = 125/150°C                               | Supply Voltage  → Time                                     |
| 2. Rate of decay of on-state commutating current (di/dt)c = -13 A/ms | Main Current (di/dt)c → Time                               |
| 3. Peak off-state voltage V <sub>D</sub> = 400 V                     | Main Voltage Time (dv/dt)c                                 |

### **Performance Curves**

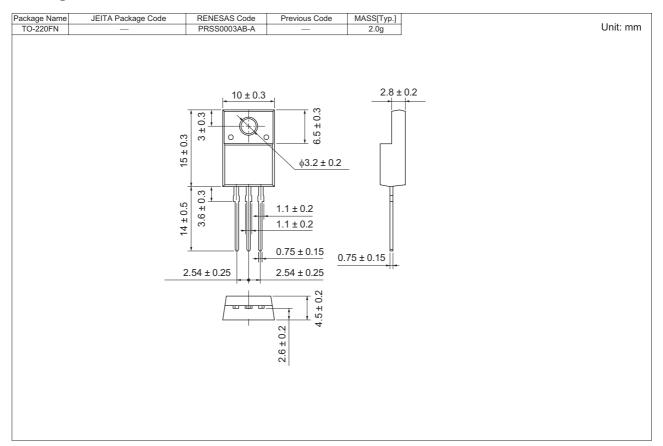








# **Package Dimensions**



## **Order Code**

| Lead form     | Standard packing        | Quantity | Standard order code           | Standard order code example |
|---------------|-------------------------|----------|-------------------------------|-----------------------------|
| Straight type | Plastic Magazine (Tube) | 50       | Type name                     | BCR25KM-12LB                |
| Lead form     | Plastic Magazine (Tube) | 50       | Type name – Lead forming code | BCR25KM-12LB -A8            |

Note: Please confirm the specification about the shipping in detail.

Renesas Technology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

- Renesas lechnology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Notes:

  1. This document is provided for reference purposes only so that Renesas customers may select the appropriate Renesas products for their use. Renesas neither makes warrantes or representations with respect to the accuracy or completeness of the information in this document nor grants any license to any intellectual property girbs to any other rights of representations with respect to the information in this document in this document of the purpose of the respect of the information in this document in the product data, diagrams, charts, programs, algorithms, and application circuit examples.

  3. You should not use the products of the technology described in this document for the purpose of military use. When exporting the products or technology described herein, you should follow the applicable export control laws and regulations, and procedures required by such laws and regulations, and procedures required to change without any plan protein. Before purchasing or using any Renesas products listed in this document, in the development is satisfied. The procedure is such as the development of the dev



### **RENESAS SALES OFFICES**

http://www.renesas.com

Refer to "http://www.renesas.com/en/network" for the latest and detailed information.

### Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd.
Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7858/7898

Renesas Technology Hong Kong Ltd.
7th Floor, North Tower, World Finance Centre, Harbour City, Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2377-3473

**Renesas Technology Taiwan Co., Ltd.** 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 3518-3399

Renesas Technology Singapore Pte. Ltd.
1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd
Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510